EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/761704	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:49
L2	1	(ultra near shallow near metal near oxide near surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:50
L3	2	((ultra near shallow) near5 (metal near oxide) near5 surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:50
L4	2	((ultra near shallow) near5 (metal near oxide) near5 (surface near channel)\)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:50
L5	2	((ultra near shallow) near5 (metal near oxide) near5 (surface near channel))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:50
L16	4	(metal near oxide near surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:53
L17	69	(metal near oxide near5 surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:53
L18	1	(metal near oxide near5 surface near channel).clm. and (high-k).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:53
L19	9	(metal near oxide near5 surface near channel).clm. and (high-k or (high dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:54

L20	3	(metal near oxide near5 surface near channel).clm. and (high-k or (high dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:54

L22	82	I21 and (surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:54
L23	41	I21 and (surface near channel). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:55
L24	33	I21 and (surface near channel). clm. and method.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:55
L25	14	I21 and (surface near channel). clm. and method.clm. and (high-k or (high near dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:56
L26	5	I21 and (surface near channel). clm. and method.clm. and (high-k or (high near dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:56
L27	8	(surface near channel).clm. and method.clm. and (high-k or (high near dielectric)).clm. and (gate adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:57
L28	2	(surface near channel).clm. and method.clm. and ((high-k or (high near dielectric)).clm. with (gate adj electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:58
L29	5424	(surface adj channel).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:58
L30	454	(surface adj channel).clm. and (gate adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:58
L31	55	(surface adj channel).clm. and (gate adj electrode).clm. and (high-k or (high near dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:58

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| L32 | 13 | (surface adj channel).clm. and (gate adj electrode).clm. and (high-k or (high near dielectric)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/09/29 21:58 |

L34	73	I33 and "surface channel"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 21:59
L35	38	I33 and "surface channel".clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:04
L36	53	well.clm. and "surface channel". clm. and (gate adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:04
L37	3	well.clm. and "surface channel". clm. and (gate adj electrode).clm. and ((high near dielectric) or high-k).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:05
L38	9	well.clm. and "surface channel". clm. and (gate adj electrode).clm. and ((high near dielectric) or high-k)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:05
L39	36	well.clm. and "surface channel" and (gate adj electrode).clm. and ((high near dielectric) or high-k)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:08
L40	347	(well same (surface adj channel) same (gate adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:09
L41	45	(well same (surface adj channel) same (gate adj electrode) same method)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:10
L42	1	(well same (surface adj channel) same (gate adj electrode) same method).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:11
L43	11	(well same (surface adj channel) same (gate adj electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:11

L44	6	(well same (surface adj channel) same (gate adj electrode)).clm. and method.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:11
L45	53	well.clm. and (surface adj channel).clm. and (gate adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:12
L46	9	well.clm. and (surface adj channel).clm. and (gate adj electrode).clm. and ((high near k) or (high-k) or (high near dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:14
L47	5424	"surface channel".clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:14
L48	532	"surface channel".clm. and "surface channel".ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:14
L49	101	"surface channel".clm. and "surface channel".ab. and (gate adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:14
L50	11	"surface channel".clm. and "surface channel".ab. and (gate adj electrode).clm. and well.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:16
L51	9	"surface channel".clm. and ((high near dielectric) or high-k or (high near k)) and (gate adj electrode).clm. and well.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:18
L52	9	(surface adj channel).clm. and ((high near dielectric) or high-k or (high near k)) and (gate adj electrode).clm. and well.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:19
L53	52	shallow near surface near channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:19

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L54	5	shallow near surface near channel and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:20
L55	5	shallow near surface near channel and (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:20
L56	47	shallow near5 surface near channel and (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:20
L57	35	shallow near5 (surface near channel) and (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:20
L58	4	shallow near5 (surface near channel).clm. and (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:21
L59	551	(surface near channel).clm. and (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:21
L60	204	(surface near channel).clm. same (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:21
L61	13	(surface near channel).clm. same (gate adj electrode) same well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:23
L62	179	(surface near channel).clm. and (buried near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:23
L63	1252	(surface near channel) and (buried near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:23

L64	769	(surface near channel) and (buried near channel) and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:23
L65	181	(surface near channel) and (buried near channel) and (gate adj electrode) and well.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:23
L66	115	(surface near channel) and (buried near channel) and (gate adj electrode).clm. and well.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:23
L67	13	(surface near channel).clm. and (buried near channel) and (gate adj electrode).clm. and well.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:28
L68	4	(metal near oxide near surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:28
L69	60	(metal near oxide near5 (surface near channel))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:28
L70	60	((metal near oxide) near5 (surface near channel))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:32
L71	2277	(surface near channel near region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:32
L72	634	(surface near channel near region) and (metal adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:32
L73	497	(surface near channel near region) and (metal adj oxide) and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:32

L74	441	(surface adj channel near region) and (metal adj oxide) and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:32
L75	421	(surface adj channel adj region) and (metal adj oxide) and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:32
L76	335	(surface adj channel adj region) and (metal adj oxide) and (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:33
L77	167	(surface adj channel adj region) and (metal adj oxide) and (gate adj electrode) and well and method.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:33
L78	10	(surface adj channel adj region) and (metal adj oxide) and (gate adj electrode) and well and method.clm. and (buried near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:34
L79	10	(surface adj channel adj region) and (metal adj oxide) and (gate adj electrode) and well and method.clm. and (buried adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:36
L80	3012	(surface adj channel) and (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:37
L81	1442	(surface adj channel) same (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:37
L82	347	(surface adj channel) same (gate adj electrode) same well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:37
L83	11	((surface adj channel) same (gate adj electrode) same well).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:37

L84	347	((surface adj channel) same (gate adj electrode) same well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:39
L85	81	((surface adj channel) same (gate adj electrode) same well) and (mosfet or mos or (metal adj oxide)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:39
L86	65	((surface adj channel) same (gate adj electrode) same well) and (mosfet or mos or (metal adj oxide)).clm. and (gate adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:40
L87	40	((surface adj channel) same (gate adj electrode) same well) and (mosfet or mos or (metal adj oxide)).clm. and (gate adj electrode).clm. and method.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:41
L88	3	((surface adj channel) same (gate adj electrode) same well) and (mosfet or mos or (metal adj oxide)).clm. and (gate adj electrode).clm. and method.clm. and (high-k or (high near dielectric near constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:42
L89	35051	(high-k or (high near k) or (high near dielectric near constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:42
L90	6570	(high-k or (high near k) or (high near dielectric near constant)) and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:42
L91	62	(high-k or (high near k) or (high near dielectric near constant)) and (gate adj electrode) and ((surface adj channel) near10 ((metal adj oxide) or mos of mosfet))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:43
L92	54	(high-k or (high near k) or (high near dielectric near constant)) and (gate adj electrode) and ((surface adj channel) near10 ((metal adj oxide) or mos of mosfet)) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:46

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L93	28	(high-k or (high near k) or (high near dielectric near constant)) with ((gate adj (dielectric or insulating)))and (gate adj electrode) and ((surface adj channel) near10 ((metal adj oxide) or mos of mosfet)) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:46
L94	28	((high-k or (high near k) or (high near dielectric near constant)) with ((gate adj (dielectric or insulating)))) and (gate adj electrode) and ((surface adj channel) near10 ((metal adj oxide) or mos of mosfet)) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 22:51
L95	3	((high-k or (high near k) or (high near dielectric near constant)) with ((gate adj (dielectric or insulating)))) and (gate adj electrode) and ((surface adj channel) near10 ((metal adj oxide) or mos of mosfet)) and well.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 23:05
L96	660	(deposit or depositing or deposited or deposition) near10 (surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 23:06
L97	527	(deposit or depositing or deposited or deposition) near10 (surface adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 23:06
L98	55	((deposit or depositing or deposited or deposition) near10 (surface adj channel)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 23:06
L99	11	((deposit or depositing or deposited or deposition) near10 (surface adj channel)).clm. and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 23:07
L100	5	(surface adj channel adj region). clm. and (buried adj channel adj region).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/29 23:08